

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1913	257/40.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 16:57
L3	369	257/642.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 16:58
L4	215	257/643.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 16:58
L5	578	257/759.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 16:58
L6	215	438/82.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 16:58
L7	650	438/99.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 17:00
L10	1036	(gate near (insulat\$3 dielectric)) and organic and (crystal near growth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 18:32
L17	21232	(gate near electrode) with (source near electrode) with (drain near electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 18:33

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L18	192	17 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 18:22
L20	188	(insulat\$3 dielectric) same organic same (crystal near growth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/03/02 18:25
L22	0	semiconductor AND (current near channel) AND (gate near (oxide insulat\$3 dielectric)) AND organic AND (crystal near growth) AND (gate near electrode) AND (source near electrode) AND (drain near electrode) AND ((conduct\$3 metal\$3) near oxide). CLM.	US-PGPUB; USPAT	OR	ON	2006/03/02 18:34